



## Description

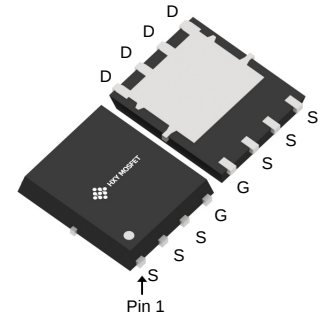
The NVMFS5834NL uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

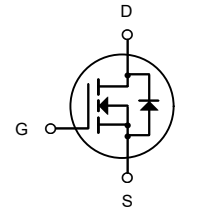
$V_{DS} = 40V$   $I_D = 55A$   
 $R_{DS(ON)} < 8.5m\Omega$   $V_{GS}=10V$

## Application

Battery protection  
Load switch  
Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

## Package Marking and Ordering Information

| Product ID  | Pack      | Brand      | Qty(PCS) |
|-------------|-----------|------------|----------|
| NVMFS5834NL | DFN5X6-8L | HXY MOSFET | 5000     |

## Absolute Maximum Ratings ( $T_c=25^{\circ}C$ unless otherwise noted)

| Symbol                 | Parameter                                  | Rating     | Units       |
|------------------------|--------------------------------------------|------------|-------------|
| $V_{DS}$               | Drain-Source Voltage                       | 40         | V           |
| $V_{GS}$               | Gate-Source Voltage                        | $\pm 20$   | V           |
| $I_D@T_c=25^{\circ}C$  | Continuous Drain Current, $V_{GS} @ 10V^1$ | 55         | A           |
| $I_D@T_c=100^{\circ}C$ | Continuous Drain Current, $V_{GS} @ 10V^1$ | 41         | A           |
| $I_{DM}$               | Pulsed Drain Current <sup>2</sup>          | 280        | A           |
| EAS                    | Single Pulse Avalanche Energy <sup>3</sup> | 76         | mJ          |
| $T_{STG}$              | Storage Temperature Range                  | -55 to 175 | $^{\circ}C$ |
| $T_J$                  | Operating Junction Temperature Range       | -55 to 175 | $^{\circ}C$ |



### Electrical Characteristics ( $T_C=25^{\circ}\text{C}$ unless otherwise noted)

| Symbol       | Parameter                                      | Conditions                                                | Min. | Typ. | Max.      | Unit      |
|--------------|------------------------------------------------|-----------------------------------------------------------|------|------|-----------|-----------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage                 | $V_{GS}=0V$ , $I_D=250\mu A$                              | 40   | ---  | ---       | V         |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=10V$ , $I_D=15A$                                  | ---  | 7.5  | 8.5       | $m\Omega$ |
|              |                                                | $V_{GS}=4.5V$ , $I_D=8A$                                  | ---  | 9    | 12        |           |
| $V_{GS(th)}$ | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=250\mu A$                          | 1.2  | 1.8  | 2.5       | V         |
| $I_{DSS}$    | Drain-Source Leakage Current                   | $V_{DS}=40V$ , $V_{GS}=0V$ , $T_J=25^{\circ}\text{C}$     | ---  | ---  | 1         | $\mu A$   |
|              |                                                | $V_{DS}=40V$ , $V_{GS}=0V$ , $T_J=55^{\circ}\text{C}$     | ---  | ---  | 5         |           |
| $I_{GSS}$    | Gate-Source Leakage Current                    | $V_{GS}=\pm 20V$ , $V_{DS}=0V$                            | ---  | ---  | $\pm 100$ | nA        |
| $R_g$        | Gate Resistance                                | $V_{DS}=0V$ , $V_{GS}=0V$ , $f=1\text{MHz}$               | ---  | 2.0  | ---       | $\Omega$  |
| $Q_g$        | Total Gate Charge (4.5V)                       | $V_{DS}=20V$ , $V_{GS}=10V$ , $I_D=10A$                   | ---  | 19.7 | ---       | nC        |
| $Q_{gs}$     | Gate-Source Charge                             |                                                           | ---  | 2.8  | ---       |           |
| $Q_{gd}$     | Gate-Drain Charge                              |                                                           | ---  | 5.1  | ---       |           |
| $T_{d(on)}$  | Turn-On Delay Time                             | $V_{DD}=15V$ , $V_{GS}=10V$ , $R_G=3.3\Omega$<br>$I_D=1A$ | ---  | 13.2 | ---       | ns        |
| $T_r$        | Rise Time                                      |                                                           | ---  | 2.2  | ---       |           |
| $T_{d(off)}$ | Turn-Off Delay Time                            |                                                           | ---  | 72   | ---       |           |
| $T_f$        | Fall Time                                      |                                                           | ---  | 4.5  | ---       |           |
| $C_{iss}$    | Input Capacitance                              | $V_{DS}=15V$ , $V_{GS}=0V$ , $f=1\text{MHz}$              | ---  | 6000 | ---       | pF        |
| $C_{oss}$    | Output Capacitance                             |                                                           | ---  | 1509 | ---       |           |
| $C_{rss}$    | Reverse Transfer Capacitance                   |                                                           | ---  | 129  | ---       |           |
| $I_S$        | Continuous Source Current <sup>1,5</sup>       | $V_G=V_D=0V$ , Force Current                              | ---  | ---  | 140       | A         |
| $V_{SD}$     | Diode Forward Voltage <sup>2</sup>             | $V_{GS}=0V$ , $I_S=1A$ , $T_J=25^{\circ}\text{C}$         | ---  | ---  | 1         | V         |

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{DD}=25V$ ,  $V_{GS}=10V$ ,  $L=0.1mH$ ,  $I_{AS}=31A$
- 4.The power dissipation is limited by  $150^{\circ}\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics

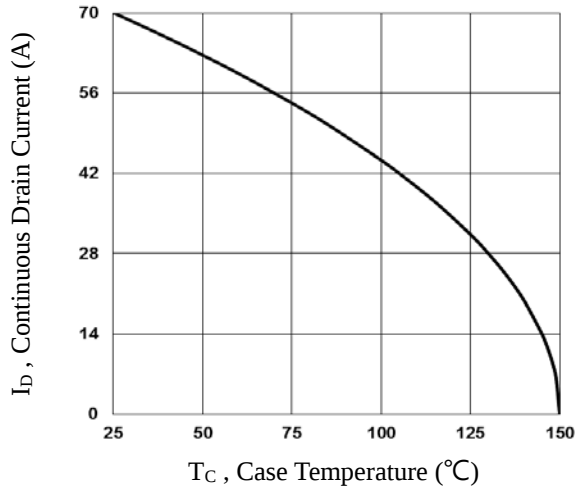


Fig.1 Continuous Drain Current vs.  $T_C$

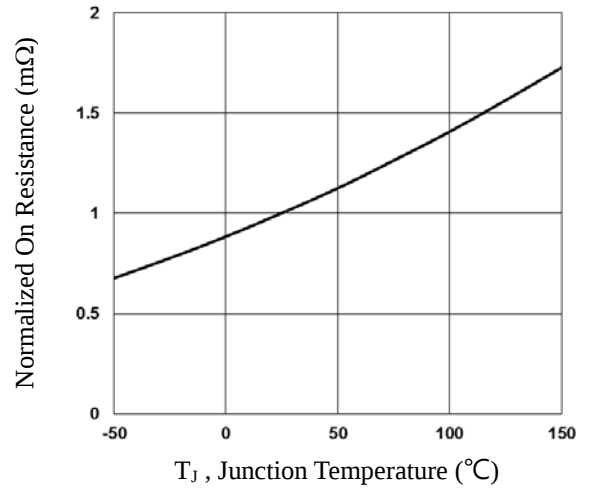


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$

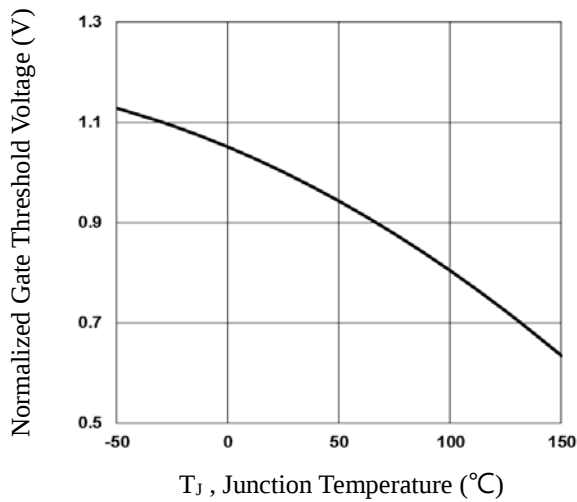


Fig.3 Normalized  $V_{th}$  vs.  $T_J$

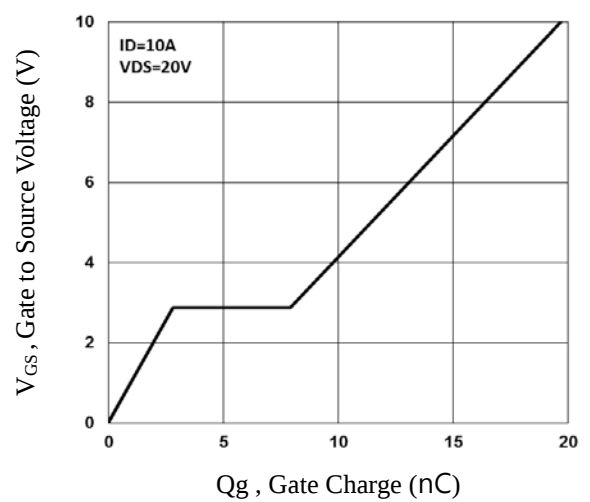


Fig.4 Gate Charge Waveform

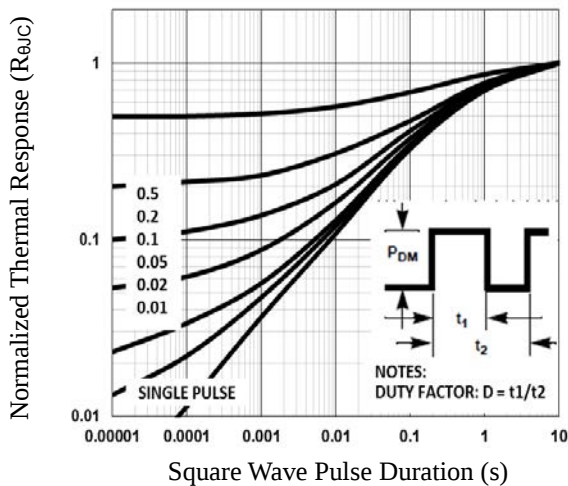


Fig.5 Normalized Transient Impedance

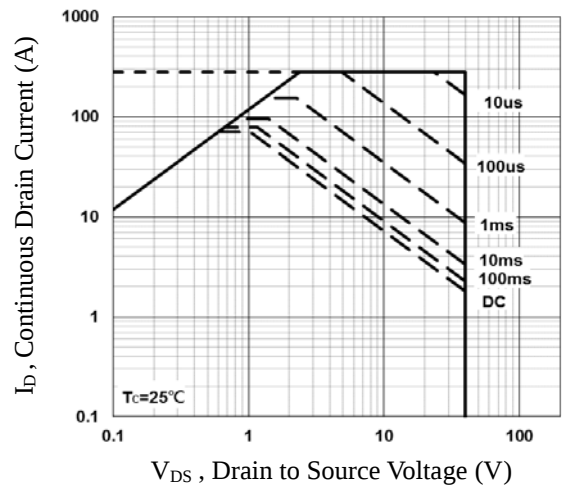


Fig.6 Maximum Safe Operation Area

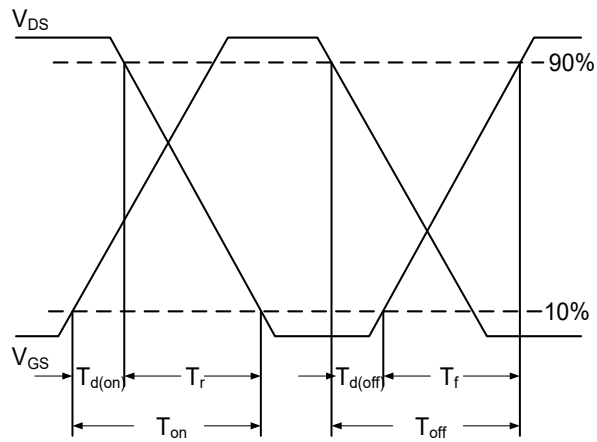


Fig.7 Switching Time Waveform

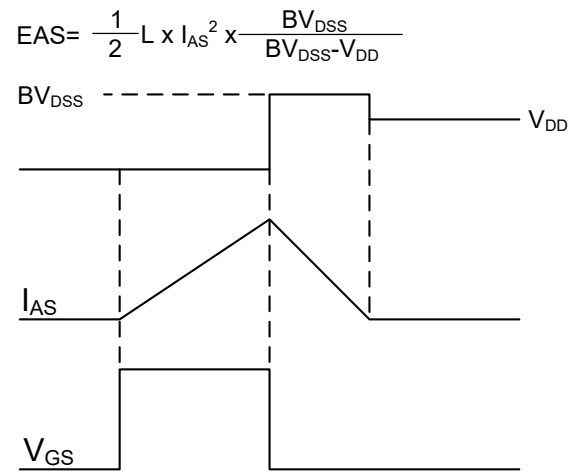
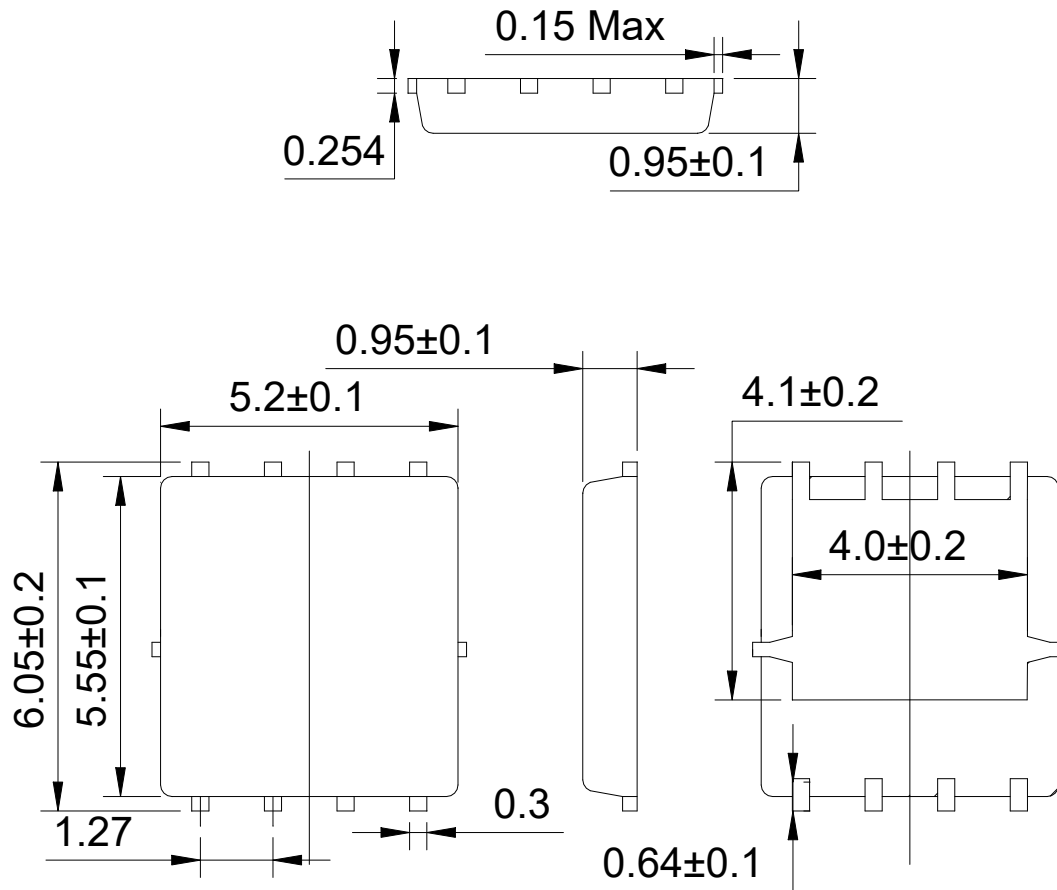


Fig.8 EAS Waveform



## DFN5X6-8L Package Information

Unit:mm





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